Counting Statistics of Single Electron Transport in a Quantum Dot

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(Received 11 October 2005; published 24 February 2006)

We have measured the full counting statistics of current fluctuations in a semiconductor quantum dot (QD) by real-time detection of single electron tunneling with a quantum point contact. This method gives direct access to the distribution function of current fluctuations. Suppression of the second moment (related to the shot noise) and the third moment (related to the asymmetry of the distribution) in a tunable semiconductor QD is demonstrated experimentally. With this method we demonstrate the ability to measure very low current and noise levels.

DOI: 10.1103/PhysRevLett.96.076605
PACS numbers: 72.70.+m, 73.23.Hk, 73.63.Kv

Current fluctuations in conductors have been extensively studied because they provide additional information compared to the average current, in particular, for interacting systems [1]. Shot noise measurements demonstrated the charge of quasiparticles in the fractional quantum Hall effect [2] and in superconductors [3]. However, to perform such measurements for semiconductor quantum dots (QDs) using conventional noise measurements techniques is very challenging. This is because of the very low currents and the corresponding low noise levels in these systems. Earlier experiments demonstrated the measurement of shot noise in nontunable QDs [4,5], but to our knowledge, no experiments have been reported in the literature in which the tunnel barriers, and thereby the knowledge, no experiments have been reported in the systems. Earlier experiments demonstrated the measurements and the corresponding low noise levels in these systems. Earlier experiments demonstrated the measurement of shot noise in nontunable QDs [4,5], but to our knowledge, no experiments have been reported in the literature in which the tunnel barriers, and thereby the coupling symmetry, could be controlled [6].

An alternative way to investigate current fluctuations, introduced by Levitov et al., is known as full counting statistics (FCS) [7]. This method relies on the evaluation of the probability distribution function of the number of electrons transferred through a conductor within a given time period. In addition to the current and the shot noise, which are the first and second moments of this distribution, this method gives access to higher order moments. Of particular interest is the third moment (skewness), which is due to breaking the time reversal symmetry at finite current. Experimentally, few attempts to measure the third moment have been made in tunnel junctions [8].

The most intuitive method for measuring the FCS of electron transport is to count electrons passing one by one through the conductor. Real-time detection of single electron transport has been experimentally investigated only very recently [9–11]. It is a challenging task since it requires a very sensitive, low-noise, and noninvasive elecrometer, as well as a high-bandwidth circuit. Several devices, such as the single electron transistor [9,10] and the quantum point contact [12–16], have been demonstrated to have high enough sensitivity to detect single electrons in a QD. But, up to now, none of these experiments were able to extract the full counting statistics of electron transport.

Here we report on the real-time detection of single electron tunneling through a QD using a quantum point contact (QPC) as a charge detector. With this method, we can directly measure the distribution function of current fluctuations in the QD by counting electrons. To our knowledge, this is the first measurement of the full counting statistics for electrons in a solid state device. In addition, we can tune the coupling of the QD with both leads and measure the respective tunneling rates. We show experimentally the suppression of the second and third moments of the current fluctuations when the QD is symmetrically coupled to the leads.

Figure 1(a) shows the structure, fabricated on a GaAs-GaAlAs heterostructure containing a two-dimensional electron gas 34 nm below the surface [density $4.5 \times 10^{15} \text{ m}^{-2}$, mobility $25 \text{ m}^2(\text{V s})^{-1}$]. An atomic force microscope (AFM) was used to locally oxidize the surface, thereby defining depleted regions below the oxide lines [17,18]. The measurements were performed in a $^3\text{He}/^4\text{He}$ dilution refrigerator with an electron temperature of about 350 mK, as determined from the width of thermally broadened Coulomb blockade resonances [6]. The charging energy of the QD is $2.1 \text{ meV}$ and the mean level spacing is $200–300 \mu\text{eV}$. The conductance of the QPC, $G_{\text{QPC}}$, was tuned close to $0.25 \times e^2/h$. We apply a dc bias voltage between the source and the drain of the QPC, $V_{\text{QPC}} = 500 \mu\text{V}$, and measure the current through the QPC, $I_{\text{QPC}}$, which depends on the number of electrons $N$ in the QD.

In order to measure the current with a charge detector, one has to avoid that electrons travel back and forth between the dot and one lead or to the other lead due to thermal fluctuations [Fig. 1(b)]. This is achieved by applying a large bias voltage between source and drain, i.e., $|\pm eV/2 - E_d| \gg k_BT$, where $E_d$ is the electrochemical potential of the dot and $V$ is the symmetrically applied bias; see Figs. 1(a) and 1(c). An example of a time trace of the QPC current in this configuration is shown in Fig. 1(d). The number of electrons in the QD fluctuates between $N$ and $N + 1$. Since this trace corresponds to the nonequilibr-
long time trace [14], can be calculated from the average of
taking the number of electrons entering the QD to the drain con-
tact. For independent tunneling events, the tunneling rates
it takes for the electron to leave the QD to the drain con-
acting a time period
of electrons entering the QD from the source contact dur-
ning a time period $t_0$, i.e., the number of down steps in
Fig. 1(d) (see arrows). We obtain the distribution function of
although this counting procedure on $m = T/t_0$
independent traces, $T = 0.5$ s being the total length of the
time trace. The resulting distribution functions are shown for
two different values of the tunneling rates in Figs. 2(a)
(b), (c) Scheme of the quantum dot in the case of equilibrium
charge fluctuations (c), (d) Time trace of the current measured through the
QPC corresponding to fluctuations of the charge of the dot
between $N$ and $N + 1$ electrons. The arrows indicate transitions
where an electron is entering the QD from the source lead.
(e) Probability density of the times $\tau_{\text{in}}$ and $\tau_{\text{out}}$ (see text)
obtained from time traces similar to the one in (d). The lines
correspond to the expected exponential dependence (see the
text), where the tunneling rates are calculated from $1/\Gamma_{S(D)} = 1/\Gamma_{\text{in(out)}} = \langle \tau_{\text{in(out)}} \rangle$.

The first application of electron counting in the nonequi-
librium regime concerns the determination of the individual
tunneling rates from the source to the QD, $\Gamma_S$, and from
the QD to the drain, $\Gamma_D$. Previous experiments determin-
ing the individual tunneling rates involved more than two
leads connected to the QD [19]. In the trace of Fig. 1(d), the
time $\tau_{\text{in}}$ corresponds to the time it takes for an electron
to enter the QD from the source contact, and $\tau_{\text{out}}$ to the time
it takes for the electron to leave the QD to the drain con-
act. For independent tunneling events, the tunneling rates
can be calculated from the average of $\tau_{\text{in}}$ and $\tau_{\text{out}}$ on a
long time trace [14], $1/\Gamma_{S(D)} = 1/\Gamma_{\text{in(out)}} = \langle \tau_{\text{in(out)}} \rangle$. To
check that the tunneling events are indeed independent, we
have compared the probability densities $p_{\tau_{\text{in}}}$ and $p_{\tau_{\text{out}}}$ with
the expected exponential behavior $p(\tau_{\text{in(out)}}) = \Gamma_{S(D)} \times
\exp(-\Gamma_{S(D)} \tau_{\text{in(out)}})$. Figure 1(e) shows good agreement
with our data. It is interesting to note that, in the case
shown in Fig. 1(e), the QD is almost symmetrically coupled. We demonstrate here a very sensitive method to
determine the symmetry of the coupling alternative to Ref. [20].

From traces similar to the one shown in Fig. 1(d), we can
directly determine the statistical properties of sequential
electron transport through the QD. We count the number $n$
of electrons entering the QD from the source contact dur-
ing a time period $t_0$, i.e., the number of down steps in
Fig. 1(d) (see arrows). We obtain the distribution function of
$n$ by repeating this counting procedure on $m = T/t_0$
independent traces, $T = 0.5$ s being the total length of the
time trace. The resulting distribution functions are shown for
two different values of the tunneling rates in Figs. 2(a)
and 2(b).

The FCS theory allows one to determine the distribution
function of the number $n$ of electrons traveling through a
conductor [7]:

$$P(n) = \int_{-\infty}^{\infty} \frac{d\chi}{\pi} e^{-S(\chi)-ax},$$  (1)

where $S(\chi)$ is the generating function, which has been
calculated for a single level QD for large bias voltage
$|\pm eV/2 - E_d| \gg k_B T$ [21]:

$$S(\chi) = [\Gamma_S + \Gamma_D - \sqrt{(\Gamma_S - \Gamma_D)^2 + 4\Gamma_S \Gamma_D e^{-\chi}}].$$  (2)

Here $\Gamma_S$ and $\Gamma_D$ are the effective tunneling rates, which
take into account any possible spin degeneracy of the levels
in the QD, and correspond to the tunneling rates we deter-
mine experimentally. We have calculated the theoretical
distribution functions for the tunneling rates measured in
the cases of Figs. 2(a) and 2(b) (solid lines). The agreement
with the experimental distribution is very good, in particu-
lar

FIG. 2 (color online). Statistical distribution of the number $n$
of electrons entering the QD during a given time $t_0$. The two
panels correspond to two different values of the tunneling rates,
obtained for different values of the gate voltage $V_G$. The time $t_0$
is chosen in order to have the same mean value of number of
events, $\langle n \rangle = 3$, for both graphs. We have checked that this
choice does not affect the results. The line shows the theoretical
distribution calculated from Eqs. (1) and (2). The tunneling rates
are determined experimentally by the method described in
Fig. 1(e), and no fitting parameters have been used for the
theoretical curves.
lar, given that no fitting parameters were used. Both graphs show a clear qualitative difference: Fig. 2(b) shows a broader and more asymmetric distribution than Fig. 2(a). We will see later that this difference comes from the different asymmetries of the tunneling rates.

In order to perform a more quantitative analysis, we calculate the three first central moments given by $\mu = \langle n \rangle$, and $\mu_i = \langle (n - \langle n \rangle)^i \rangle$ for $i = 2, 3$, where $\langle \cdots \rangle$ represents the mean over $T/t_0$ periods of length $t_0$. The first moment (mean) gives access to the mean current, $I = e\mu/t_0$, and the second central moment (variance) to the shot noise, $S_2 = 2e^2\mu_2/t_0$ (for $t_0$ much larger than the correlation time). We are also interested in the third central moment, $\mu_3$, which gives the asymmetry of the distribution function around its maximum (skewness). An important difference to previous measurements of the third cumulant is that our method can be used to extract any higher order cumulants. For the data presented here, the accuracy of the higher cumulants is limited by the short length of the time traces.

We first focus on the mean $\mu$ of the distribution. By measuring $\mu$ as a function of the voltage applied on gate $G1$ and the bias voltage $V$, we can construct the so-called Coulomb diamonds [see Fig. 3(a)]. The Coulomb diamonds describe the charge stability of the QD, normally measured in standard transport experiments [6]. Here, we present a novel way of measuring Coulomb blockade diamonds by time-resolved detection of the electrons using a noninvasive charge detector. We observe clear Coulomb blockade regions as well as regions of finite current. As we increase the bias voltage, we see steps in the current. The first step in Fig. 3(b) (see left arrow) corresponds to the alignment of the chemical potential of the source contact with the ground state in the QD, and the following steps with excited states in the QD. From the resolution of the Coulomb diamonds, we see that the sample is stable enough such that background charge fluctuations do not play a significant role [22].

In addition to the mean, we have calculated the second and third central moments of the electron counting statistics. These two moments are shown in Fig. 3(b) for $V_{G1} = -44$ mV as a function of the bias voltage. The second moment (blue dotted line) reproduces the steps seen in the current. These two moments can be represented by their reduced quantities $\mu_2/\mu$ (known as the Fano factor) and $\mu_3/\mu$, as shown in Fig. 3(c). Both normalized moments are almost independent of the bias voltage, and correspond to a reduction compared to the values $\mu_2/\mu = \mu_3/\mu = 1$ expected for classical fluctuations with Poissonian counting statistics. Super-Poissonian noise [23] is not expected in our configuration.

In a QD, one expects a reduction of the moments due to the fact that when one electron occupies the QD, a second electron cannot enter. This leads to correlations in the current fluctuations and to a reduction of the noise. The reduction is maximal when the tunnel barriers are symmetric. The reduction is maximal when the tunnel barriers are symmetric.

FIG. 3 (color online). (a) Average number of electrons entering the QD, $\mu$, measured as a function of the gate voltage $V_{G1}$ and the bias voltage $V$. Far from the edges of the Coulomb blockade region, i.e., for $| \pm eV/2 - E_d | \gg k_BT$, the fluctuations of $n$ are directly related to current fluctuations. The dashed line corresponds to the cross section shown in panel (b). (b) Three first moments of the fluctuations of $n$ as a function of the bias voltage $V$ and at a given gate voltage $V_{G1} = -44$ mV. The ground state (GS) as well as two excited states (ES) are clearly visible. The moments are scaled so that $\mu$ corresponds to the number of electrons entering the QD per second. In the gray region, the condition $| \pm eV/2 - E_d | \gg k_BT$ is not valid, and the number of electrons entering the QD cannot be taken as the current flowing through the QD. The width of this region is $9 \times k_BT/e = 300 \mu$V, determined from the width for which the Fermi distribution is between 0.01 and 0.99. (c) Normalized second and third moments as a function of the bias voltage $V$ and at a given gate voltage $V_{G1} = -44$ mV.

For an asymmetrically coupled QD, the transport is governed by the slow barrier and the noise recovers the value for a single tunneling barrier. The normalized moments for a single level QD at large bias voltage can be expressed as a function of the asymmetry of the tunneling rates, $a = (\Gamma_S - \Gamma_D)/(\Gamma_S + \Gamma_D)$ [21]:

$$\frac{\mu_2}{\mu} = \frac{1}{2}(1 + a^2) \quad \text{and} \quad \frac{\mu_3}{\mu} = \frac{1}{4}(1 + 3a^4).$$

The second central moment recovers earlier calculations of the Fano factor in a QD [24]. We see in these equations that both moments are reduced for a symmetrically coupled QD (i.e., $a = 0$), and tend to the Poissonian values for an asymmetrically coupled QD (i.e., $a = \pm 1$).

Reduction of the second moment (shot noise) due to the Coulomb blockade has already been reported in the case of asymmetrically coupled QDs [4,5]. In these experiments, reduction of the shot noise occurs due to bias voltage dependent effective tunneling rates [24]. Here we report the reduction of the second as well as the third moment for a fully controllable QD. In particular, we are able to continuously change the tunneling rates: by changing the gate voltage $V_{G1}$, we change the chemical potential in the QD, and also the asymmetry of the coupling by changing the
amplifiers (typically current noise levels. Conventional measurement tech-
is not sensitive to the noise and drifts of the experimental measurements obtained with conventional current meters. In addition, as a limited is mainly given by the length of the time trace electrons per second, i.e., less than 1 aA. The low-current range up to 5 fA, and we can measure currents as low as a few fA, as a function of the asymmetry, \( a \), as a function of \( V_{G1} \).

opening of the source lead. The tunneling rates can be directly measured as described in Fig. 1(e), and the inset of Fig. 4(b) shows the variation of asymmetry with gate voltage in the region of interest. In Figs. 4(a) and 4(b), we show the normalized second and third central moments as a function of the asymmetry, \( a \). The experimental data follow the theoretical predictions given by Eq. (3) very well. We note, in particular, that no fitting parameters have been used since the tunneling rates are determined experimentally.

Our ability to measure the counting statistics of electron transport relies on the high sensitivity of the QPC as a charge detector. The counting process that we demonstrate in this Letter was not possible in previous experiments with the accuracy required for performing a statistical analysis [10]. Given the bandwidth of our experimental setup, \( \Delta f = 30 \text{ kHz} \), the method allows one to measure currents up to 5 fA, and we can measure currents as low as a few electrons per second, i.e., less than 1 aA. The low-current limitation is mainly given by the length of the time trace and the stability of the QD, and is well below what can be measured with conventional current meters. In addition, as we directly count electrons one by one, this measurement is not sensitive to the noise and drifts of the experimental setup. It is also a very sensitive way of measuring low-current noise levels. Conventional measurement techniques are usually limited by the current noise of the amplifiers (typically \( 10^{-29} \text{ A}^2/\text{Hz} \) [2,4,5]: here we demonstrate a measurement of the noise power with a sensitivity better than \( 10^{-35} \text{ A}^2/\text{Hz} \).

In conclusion, we have measured current fluctuations in a semiconductor QD, using a QPC to detect single electron traveling through the QD. We show experimentally the reduction of the second and third moments of the distribu-
tion when the QD is symmetrically coupled to the leads. This ability to measure current fluctuations in a QD, as well as the very low-noise level we demonstrate here, opens new possibilities towards measuring electronic entanglement in quantum dot systems [25,26].

The authors thank W. Belzig for drawing their attention to the measurement of the full counting statistics. Financial support from the Swiss Science Foundation (Schweizerischer Nationalfonds) via NCCR Nanoscience and from the EU Human Potential Program financed via the Bundesministerium für Bildung und Wissenschaft is gratefully acknowledged.

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